Vishay Semiconductors

COMPLIANT

HALOGEN

Thyristor High Voltage, Surface Mount Phase Control SCR, 16 A



PRIMARY CHARACTERISTICS							
I _{T(AV)}	10 A						
V _{DRM} /V _{RRM}	800 V, 1200 V						
V _{TM}	1.4 V						
I _{GT}	60 mA						
TJ	-40 °C to 125 °C						
Package	D ² PAK (TO-263AB)						
Circuit configuration	Single SCR						

FEATURES

 Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C

 Designed and qualified according JEDEC®-JESD 47

 Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

DESCRIPTION

The VS-16TTS..S-M3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS									
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS									
NEMA FR-4 or G-10 glass fabric-based epoxy with 4 oz. (140 μm) copper	2.5	3.5							
Aluminum IMS, R _{thCA} = 15 °C/W	6.3	9.5	A						
Aluminum IMS with heatsink, R _{thCA} = 5 °C/W	14.0	18.5							

Note

• T_A = 55 °C, T_J = 125 °C, footprint 300 mm²

MAJOR RATINGS AND CHARACTERISTICS									
PARAMETER	TEST CONDITIONS	VALUES	UNITS						
I _{T(AV)}	Sinusoidal waveform	10	۸						
I _{RMS}		16	A						
V _{RRM} /V _{DRM}		800 to 1200	V						
I _{TSM}		200	A						
V _T	10 A, T _J = 25 °C	1.4	V						
dV/dt		500	V/µs						
dl/dt		150	A/µs						
TJ		-40 to +125	°C						

VOLTAGE RATINGS									
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA						
VS-16TTS08S-M3	800	800	- 10						
VS-16TTS12S-M3	1200	1200							



Vishay Semiconductors

ABSOLUTE MAXIMUM RATINGS		T		1,741		I
PARAMETER	SYMBOL		TEST CONDITIONS	VAL	UNITS	
	01111202	.20. 00.15.110.10			MAX.	011110
Maximum average on-state current	I _{T(AV)}	$T_{\rm C} = 98 {\rm ^{\circ}C}, {\rm ^{\circ}}$	80° conduction, half sine wave	1		
Maximum RMS on-state current	I _{RMS}			1	6	Α
Maximum peak, one-cycle,	1	10 ms sine p	ulse, rated V _{RRM} applied	1	70	_ ^
non-repetitive surge current	I _{TSM}	10 ms sine p	ulse, no voltage reapplied	20	00	
Maximum 12t for fusing	I ² t	10 ms sine p	ulse, rated V _{RRM} applied	144		A2-
Maximum I ² t for fusing	1-1	10 ms sine p	200		- A ² s	
Maximum I ² √t for fusing	I ² √t	t = 0.1 ms to	10 ms, no voltage reapplied	2000		A²√s
Maximum on-state voltage drop	V_{TM}	10 A, T _J = 25	10 A, T _J = 25 °C			V
On-state slope resistance	r _t	T 105 %		24.0		mΩ
Threshold voltage	V _{T(TO)}	T _J = 125 °C		1.1		V
Maximum various and divest leakers arrant	1 /1	T _J = 25 °C	$V_R = \text{rated } V_{RRM} / V_{DRM}$	0	.5	
Maximum reverse and direct leakage current	I_{RM}/I_{DM}	T _J = 125 °C	T _J = 125 °C		10	
Holding current	I _H	Anode suppl T _J = 25 °C	Anode supply = 6 V, resistive load, initial I_T = 1 A, I_J = 25 °C		150	mA
Maximum latching current	ΙL	Anode supply = 6 V, resistive load, T _J = 25 °C				
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J$ max. linear to 80 % $V_{DRM} = R_g - k = open$			500	
Maximum rate of rise of turned-on current	dl/dt				150	

TRIGGERING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum peak gate power	P _{GM}		8.0	W				
Maximum average gate power	P _{G(AV)}		2.0	VV				
Maximum peak positive gate current	+ I _{GM}		1.5	Α				
Maximum peak negative gate voltage	- V _{GM}		10	V				
		Anode supply = 6 V, resistive load, T _J = - 10 °C	90	mA				
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	60					
		Anode supply = 6 V, resistive load, T _J = 125 °C	35					
		Anode supply = 6 V, resistive load, T _J = - 10 °C	3.0					
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	2.0	V				
		Anode supply = 6 V, resistive load, T _J = 125 °C	1.0	V				
Maximum DC gate voltage not to trigger	V_{GD}	T 105 °C V Detectoralise	0.25					
Maximum DC gate current not to trigger	I_{GD}	T _J = 125 °C, V _{DRM} = Rated value	2.0	mA				

SWITCHING								
PARAMETER SYMBOL TEST CONDITIONS VALUES UN								
Typical turn-on time	t _{gt}	$T_J = 25 ^{\circ}C$	0.9					
Typical reverse recovery time	t _{rr}	T _{.1} = 125 °C	4	μs				
Typical turn-off time	t _q	1J = 125 C	110					

Vishay Semiconductors

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	VALUES	UNITS							
Maximum junction and storage temperature range	T _J , T _{Stg}		-40 to +125	°C					
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	1.3	20044					
Typical thermal resistance, junction to ambient	R _{thJA}	PCB mount (1)	40	°C/W					
Approximate weight			2	g					
Approximate weight			0.07	oz.					
Marking device		Case style D ² PAK (TO-263AB)	16TTS08S						
Marking device		Case style D-FAR (10-203AB)	16TTS12S						

Note

⁽¹⁾ When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 µm) copper 40 °C/W. For recommended footprint and soldering techniques refer to application note #AN-994

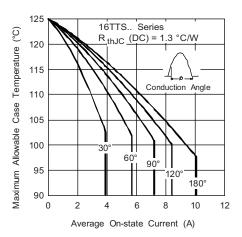


Fig. 1 - Current Rating Characteristics

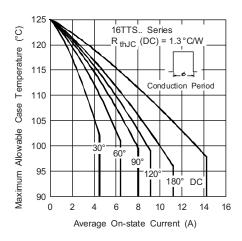


Fig. 2 - Current Rating Characteristics

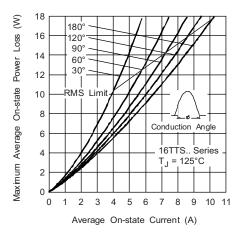


Fig. 3 - On-State Power Loss Characteristics

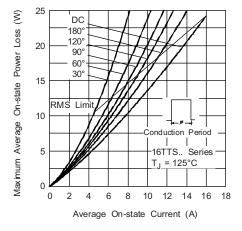


Fig. 4 - On-State Power Loss Characteristics

www.vishay.com

Vishay Semiconductors

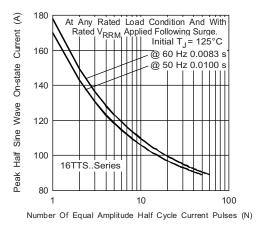


Fig. 5 - Maximum Non-Repetitive Surge Current

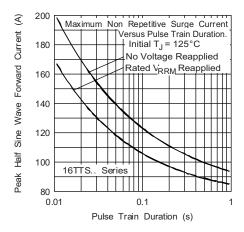


Fig. 6 - Maximum Non-Repetitive Surge Current

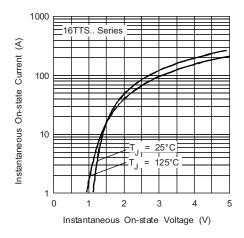


Fig. 7 - On-State Voltage Drop Characteristics

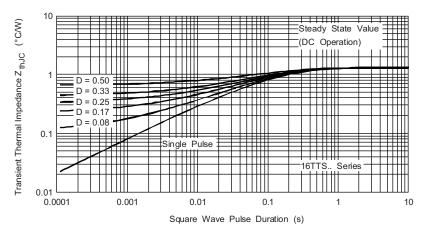


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

Vishay Semiconductors

www.vishay.com

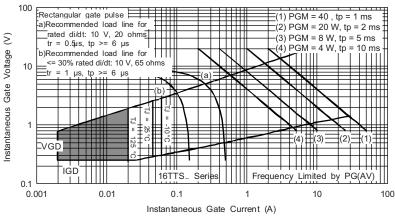
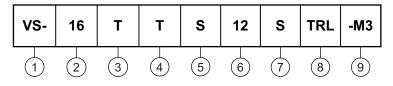


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code



- 1 Vishay Semiconductors product
- 2 Current rating
- Circuit configuration:
 - T = single thyristor
- 4 Package:
 - $T = D^2PAK (TO-263AB)$
- 5 Type of silicon:
 - S = standard recovery rectifier
- Voltage rating: voltage code x 100 = V_{RRM} 08 = 800 V 12 = 1200 V
- 7 S = surface mountable
- 8 • None = tube
 - TRL = tape and reel (left oriented)
 - TRR = tape and reel (right oriented)
- 9 -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)								
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION						
VS-16TTS08S-M3	50	Antistatic plastic tubes						
VS-16TTS08STRL-M3	800	13" diameter plastic tape and reel						
VS-16TTS08STRR-M3	800	13" diameter plastic tape and reel						
VS-16TTS12S-M3	50	Antistatic plastic tubes						
VS-16TTS12STRL-M3	800	13" diameter plastic tape and reel						
VS-16TTS12STRR-M3	800	13" diameter plastic tape and reel						

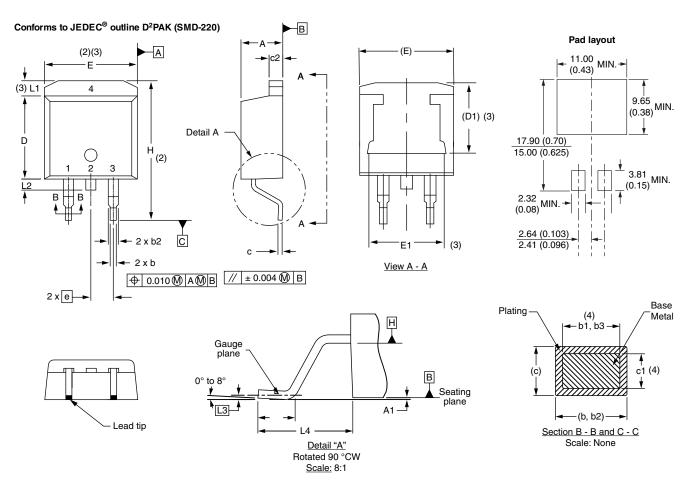
LINKS TO RELATED DOCUMENTS							
Dimensions <u>www.vishay.com/doc?96164</u>							
Part marking information	www.vishay.com/doc?95444						
Packaging information	www.vishay.com/doc?96424						
SPICE model	www.vishay.com/doc?96772						



Vishay Semiconductors

D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	ETERS	INC	HES	NOTES	NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

Revision: 13-Jul-17 Document Number: 96164



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.